

Description

The SXESDUC5D5VB protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.

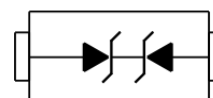
Feature

100W peak pulse power per line ($t_p = 8/20\mu s$)
 SOD-523 package
 Replacement for MLV(0603)
 Bidirectional configurations
 Response time is typically $< 1ns$
 High ESD protection
 Low clamping voltage
 RoHS compliant
 Transient protection for data lines to
 IEC 61000-4-2(ESD) $\pm 18kV$ (air), $\pm 15kV$ (contact);
 IEC 61000-4-4(EFT) 40A (5/50ns)

Mechanical Characteristics

Lead finish:100% matte Sn(Tin)
 Mounting position: Any
 Qualified max reflow temperature:260℃
 Device meets MSL 1 requirements
 Pure tin plating: 7 ~ 17 μm
 Pin flatness: $\leq 3mil$

SOD-523

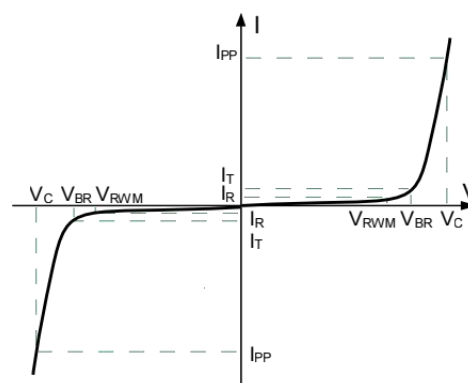


Applications

Cellular phones
 Portable devices
 Digital cameras
 Power supplies
 Bidirectional configurations

Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance
I_F	Forward Current
V_F	Forward Voltage @ I_F



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	V_{RWM}				5	V
Breakdown Voltage	V_{BR}	$I_t = 1mA$	5.6		8.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 5V$, $T=25^{\circ}C$			1.0	μA
Clamping Voltage ¹⁾	V_C	$TLP = 16A$, $t_p = 100ns$		28.1		V
Clamping Voltage ²⁾	V_C	$I_{PP} = 1A$, $t_p = 8/20\mu s$			12	V
	V_C	$I_{PP} = 5A$, $t_p = 8/20\mu s$			20	V
Junction Capacitance	C_j	$V_R=0V$, $f = 1MHz$		0.4		pF

Notes:

1. TLP parameter: $Z_0=50\Omega$, $t_p=100ns$, $t_r=2ns$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

2. Non-repetitive current pulse, according to IEC61000-4-5.

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{PP}	100	W
Peak Pulse Current ($t_p = 8/20\mu s$)	I_{PP}	5	A
Lead Soldering Temperature	T_L	260 (10 sec)	$^{\circ}C$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^{\circ}C$
ESD Protection-Contact Discharge	V_{ESD}	± 15	kV
ESD Protection-Air Discharge	V_{ESD}	± 18	kV

Typical Characteristics

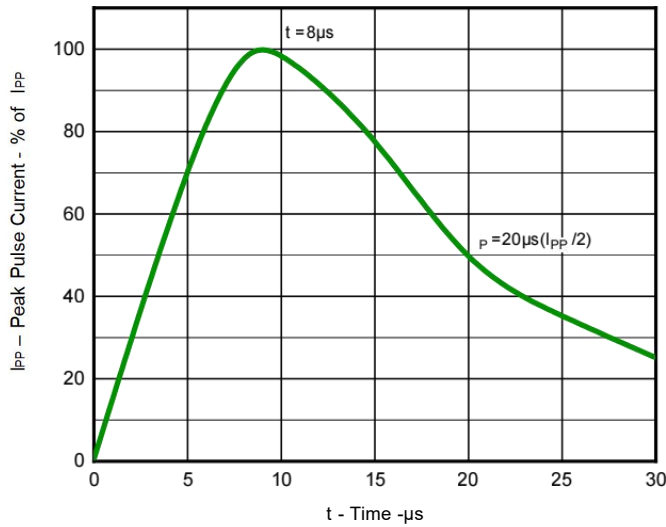


Fig 1. Pulse Waveform (8/20 μs)

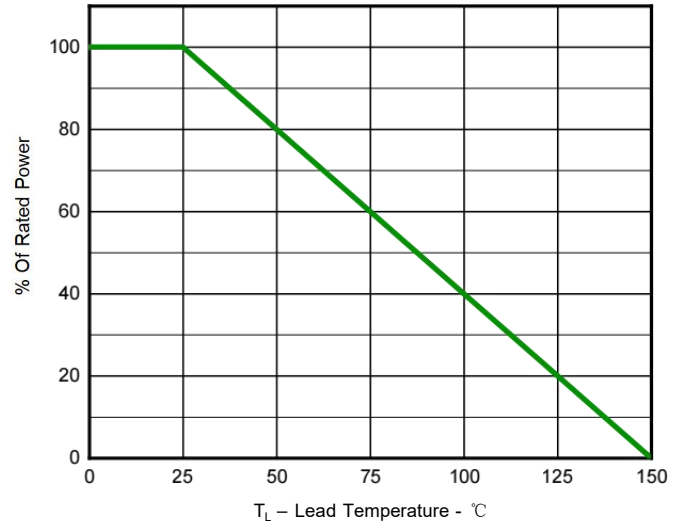


Fig 2. Power Derating Curve

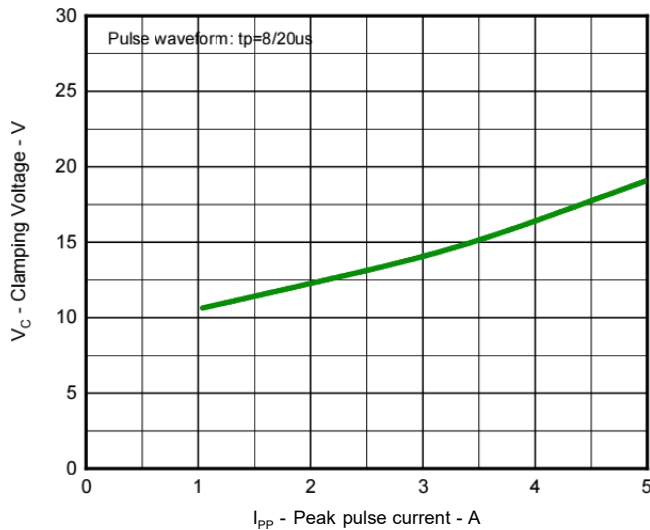


Fig 3. Clamping voltage vs. Peak pulse current

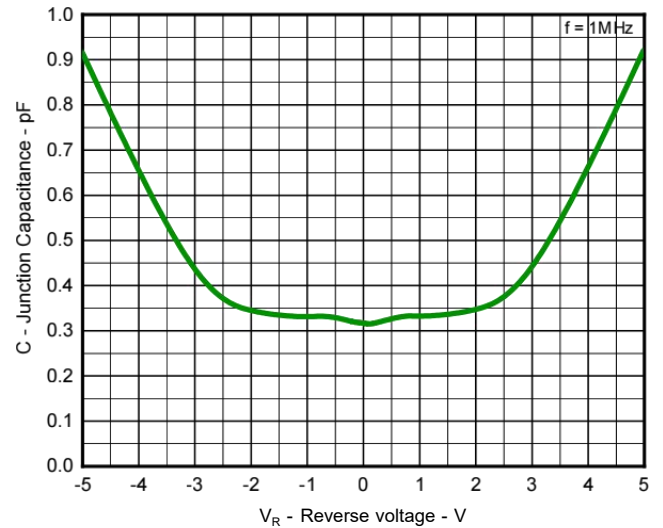


Fig 4. Capacitance vs. Reverse voltage

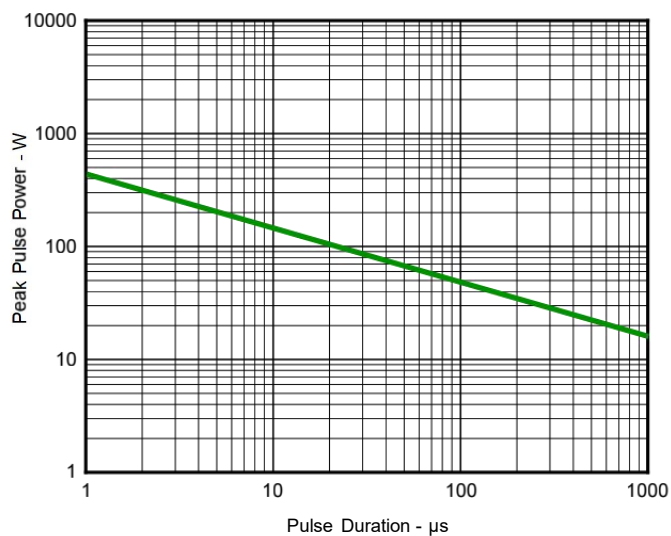


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

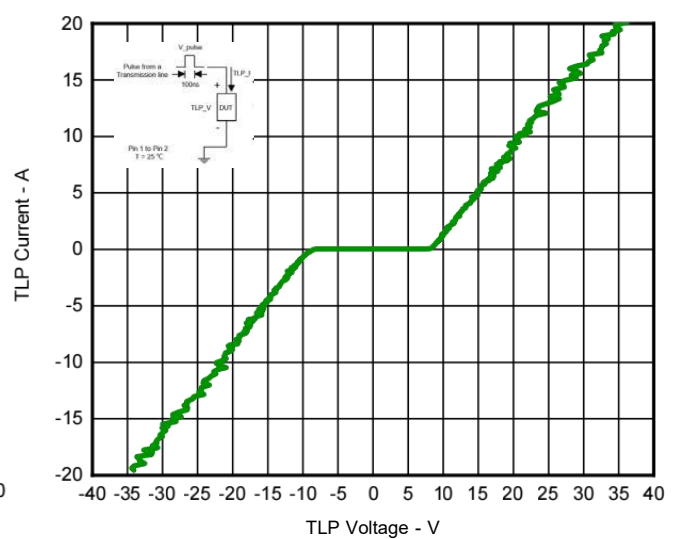
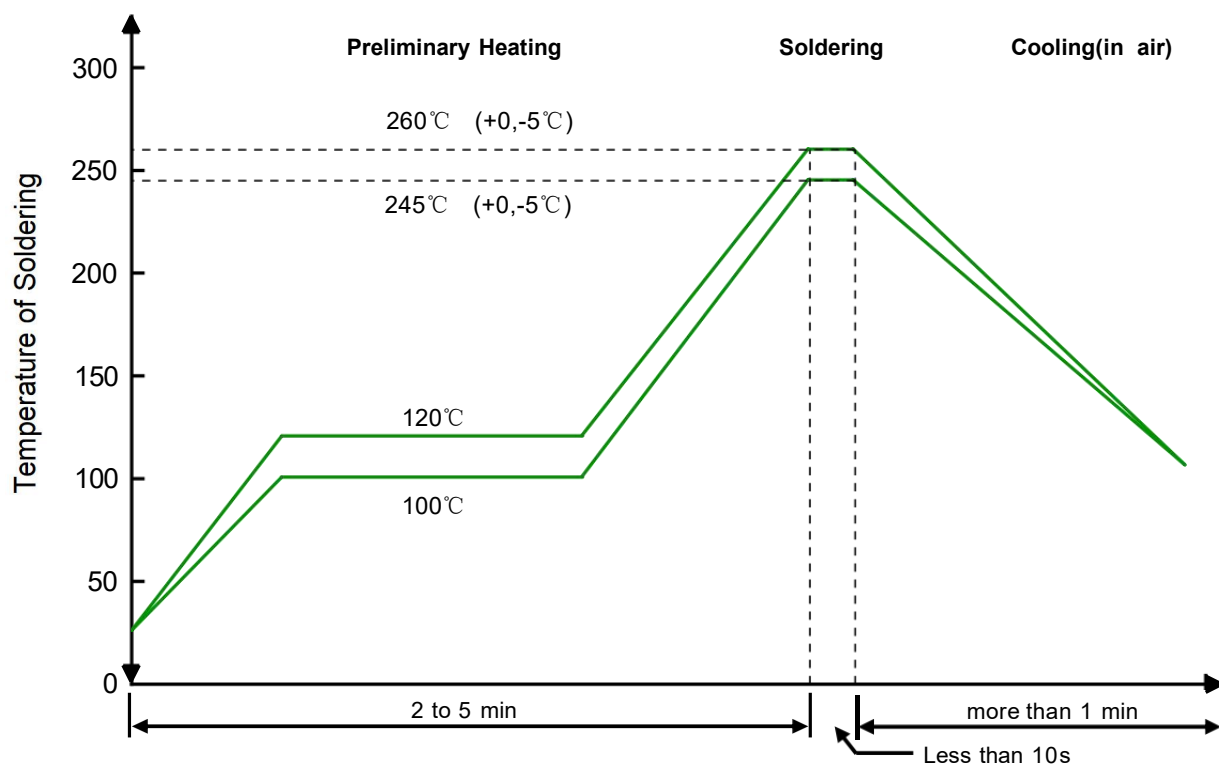


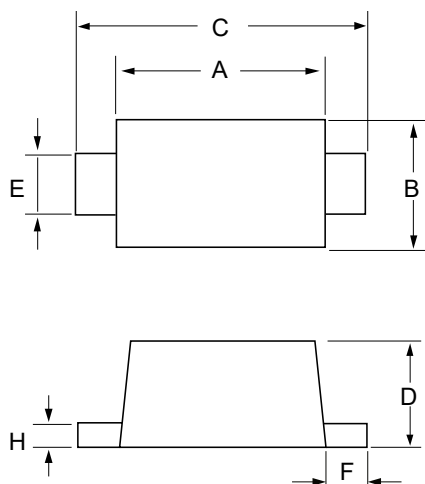
Fig 6. TLP Measurement

Solder Reflow Recommendation

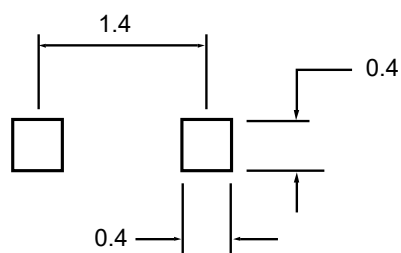


Remark: Pb free for 260 °C ; Pb for 245 °C .

Product dimension (SOD-523)



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.043	0.051	1.10	1.30
B	0.028	0.035	0.70	0.90
C	0.059	0.067	1.50	1.70
D	0.020	0.028	0.50	0.70
E	0.010	0.014	0.25	0.35
F	0.006	0.010	0.15	0.25
H	0.0028	0.0079	0.07	0.20



Unit:mm

Ordering information

Device	Package	Shipping
TAPING	SOD-523 (Pb-Free)	3000 / Tape & Reel